## NSN 5961-01-444-8190

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Photo Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-444-8190 **Inclosure Material:** Metal **Overall Length:** Between 0.140 inches and 0.150 inches **Mounting Facility Quantity:** Joint Electronic Device Engineering Council/jedec/case Outline Designation: To-46 **Mounting Method:** Unthreaded hole **Semiconductor Material:** Gallium arsenide **Voltage Rating In Volts Per Characteristic:** 2.0 forward voltage, dc and 2.0 reverse voltage, instantaneous **Current Rating Per Characteristic:** 100.00 milliamperes source cutoff current preset **Maximum Operating Tempurature Per Measurement Point:** 125.0 degrees celsius ambient air **Terminal Type And Quantity:** 2 uninsulated wire lead Shelf Life: N/a **Unit Of Measure: Demilitarization:** No Fiig: